

## Advanced Power MOSFET

## SSR/U3055LA

### FEATURES

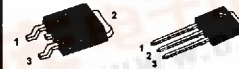
- Logic-Level Gate Drive
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 10  $\mu$ A (Max.) @  $V_{DS} = 60V$
- Lower  $R_{DS(ON)}$  : 0.124  $\Omega$  (Typ.)

$$BV_{DSS} = 60 V$$

$$R_{DS(on)} = 0.165 \Omega$$

$$I_D = 8 A$$

D-PAK I-PAK



1. Gate 2. Drain 3. Source

### Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
$V_{DSS}$	Drain-to-Source Voltage	60	V
$I_D$	Continuous Drain Current ( $T_c=25^\circ C$ )	8	A
	Continuous Drain Current ( $T_c=100^\circ C$ )	5	
$I_{DM}$	Drain Current-Pulsed ①	28	A
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulsed Avalanche Energy ②	55	mJ
$I_{AR}$	Avalanche Current ①	8	A
$E_{AR}$	Repetitive Avalanche Energy ①	1.8	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.5	V/ns
$P_D$	Total Power Dissipation ( $T_A=25^\circ C$ ) *	2.5	W
	Total Power Dissipation ( $T_c=25^\circ C$ )	18	W
	Linear Derating Factor	0.14	W/ $^\circ C$
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	- 55 to +150	$^\circ C$
$T_L$	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

### Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	6.73	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient *	--	50	
$R_{\theta JA}$	Junction-to-Ambient	--	110	

\* When mounted on the minimum pad size recommended (PCB Mount).

**SAMSUNG**

ELECTRONICS

# SSR/U3055LA

## N-CHANNEL POWER MOSFET

### Electrical Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
$BV_{DSS}$	Drain-Source Breakdown Voltage	60	--	--	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	0.046	--	V/°C	$I_D=250\mu A$ See Fig 7
$V_{GS(th)}$	Gate Threshold Voltage	1.0	--	2.0	V	$V_{DS}=5V, I_D=250\mu A$
$I_{GSS}$	Gate-Source Leakage, Forward	--	--	100	nA	$V_{GS}=20V$
	Gate-Source Leakage, Reverse	--	--	-100	nA	$V_{GS}=-20V$
$I_{DSS}$	Drain-to-Source Leakage Current	--	--	10	$\mu A$	$V_{DS}=60V$
		--	--	100		$V_{DS}=48V, T_C=125^\circ C$
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	0.165	$\Omega$	$V_{GS}=5V, I_D=4A$ ④
$g_{fs}$	Forward Transconductance	--	4.7	--	$\text{S}$	$V_{DS}=30V, I_D=4A$ ④
$C_{iss}$	Input Capacitance	--	265	345	pF	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$ See Fig 5
$C_{oss}$	Output Capacitance	--	100	115		
$C_{rss}$	Reverse Transfer Capacitance	--	37	45		
$t_{d(on)}$	Turn-On Delay Time	--	10	30	ns	$V_{DD}=30V, I_D=10A,$ $R_G=12\Omega$ See Fig 13 ④ ⑤
$t_r$	Rise Time	--	16	45		
$t_{d(off)}$	Turn-Off Delay Time	--	21	55		
$t_f$	Fall Time	--	15	40		
$Q_g$	Total Gate Charge	--	7.2	10	nC	$V_{DS}=48V, V_{GS}=5V,$ $I_D=10A$ See Fig 6 & Fig 12 ④ ⑤
$Q_{gs}$	Gate-Source Charge	--	2.6	--		
$Q_{gd}$	Gate-Drain( "Miller" ) Charge	--	3.2	--		

### Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
$I_S$	Continuous Source Current	--	--	8	A	Integral reverse pn-diode in the MOSFET
$I_{SM}$	Pulsed-Source Current ①	--	--	28		
$V_{SD}$	Diode Forward Voltage ④	--	--	1.5	V	$T_J=25^\circ C, I_S=8A, V_{GS}=0V$
$t_{rr}$	Reverse Recovery Time	--	50	--	ns	$T_J=25^\circ C, I_F=10A$
$Q_{rr}$	Reverse Recovery Charge	--	0.075	--	$\mu C$	$di_F/dt=100A/\mu s$ ④

#### Notes :

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ②  $L=1\text{mH}, I_{AS}=8A, V_{DD}=25V, R_G=27\Omega,$  Starting  $T_J=25^\circ C$
- ③  $I_{SD} \leq 10A, di/dt \leq 200A/\mu s, V_{DD} \leq BV_{DSS},$  Starting  $T_J=25^\circ C$
- ④ Pulse Test : Pulse Width =  $250\mu s,$  Duty Cycle  $\leq 2\%$
- ⑤ Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

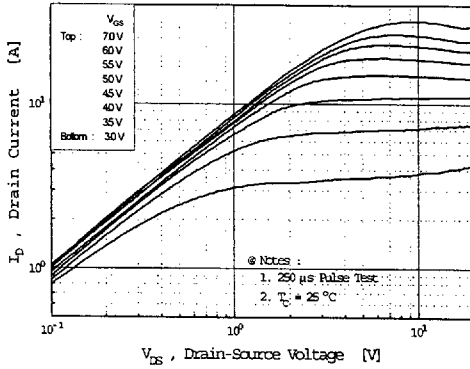


Fig 2. Transfer Characteristics

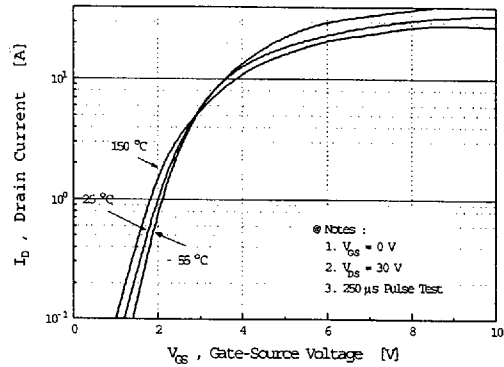


Fig 3. On-Resistance vs. Drain Current

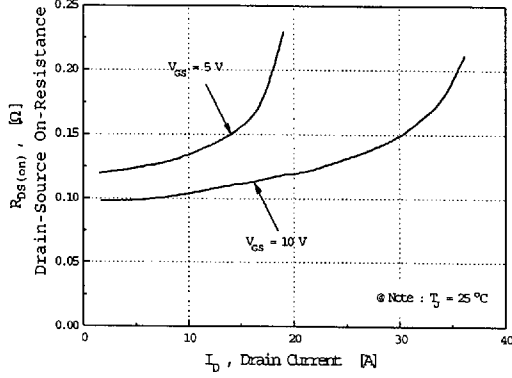


Fig 4. Source-Drain Diode Forward Voltage

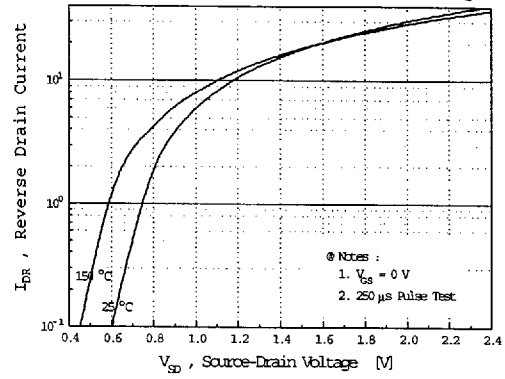


Fig 5. Capacitance vs. Drain-Source Voltage

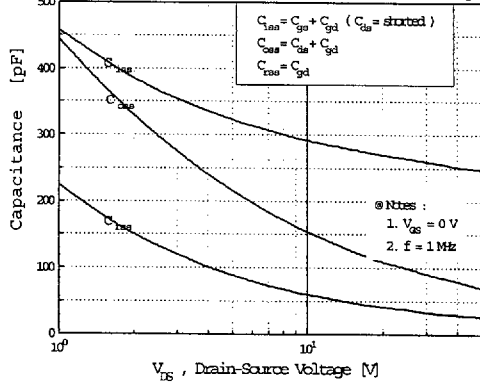
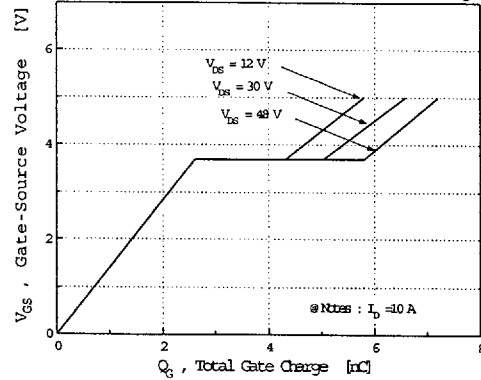
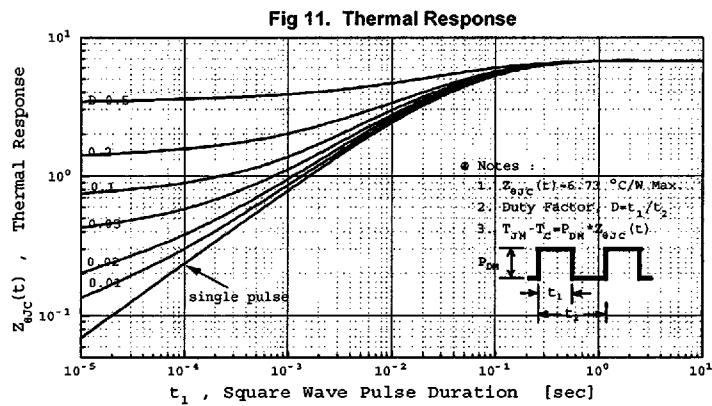
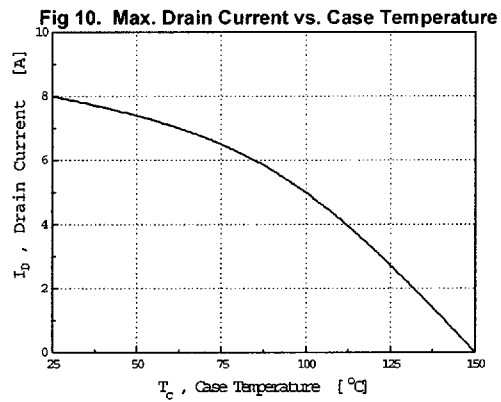
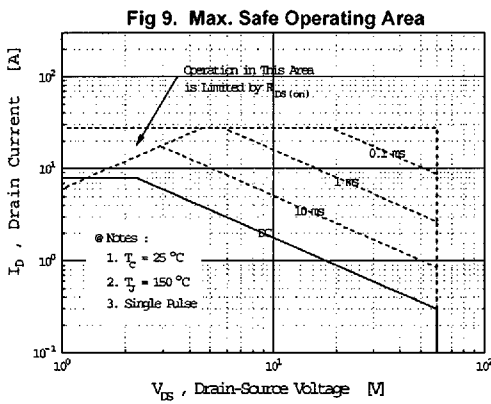
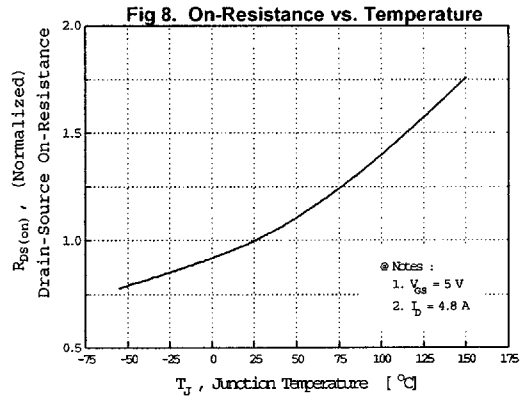
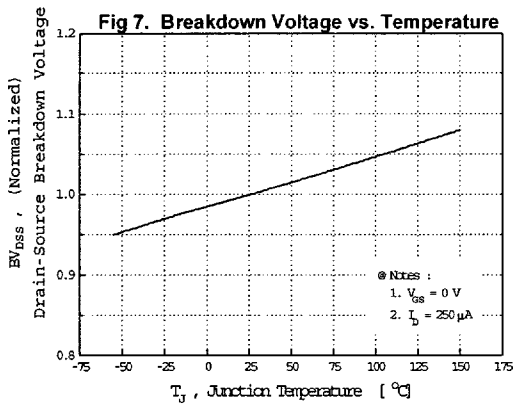


Fig 6. Gate Charge vs. Gate-Source Voltage

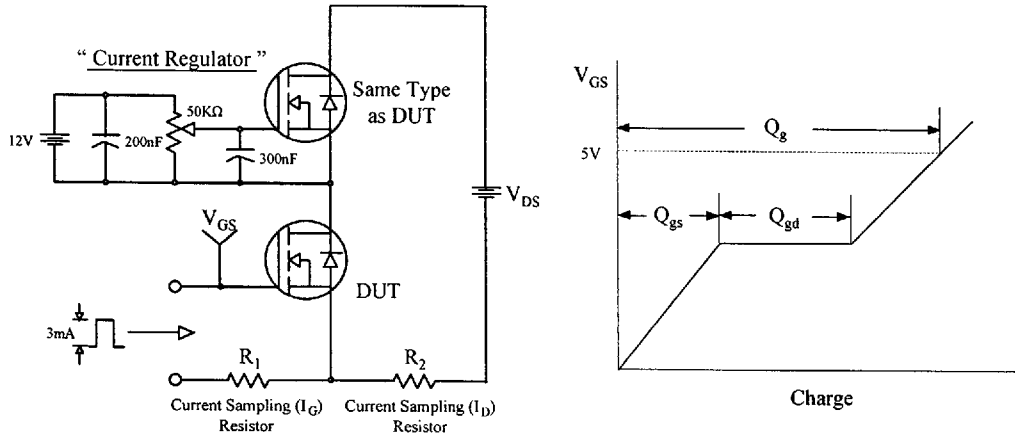


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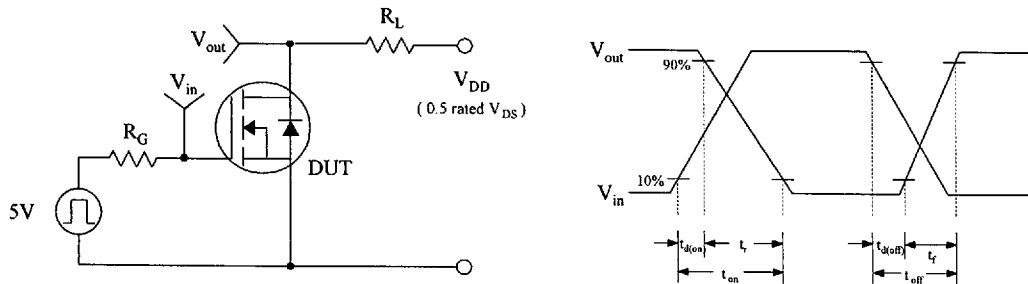
# N-CHANNEL POWER MOSFET



**Fig 12. Gate Charge Test Circuit & Waveform**



**Fig 13. Resistive Switching Test Circuit & Waveforms**



**Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms**

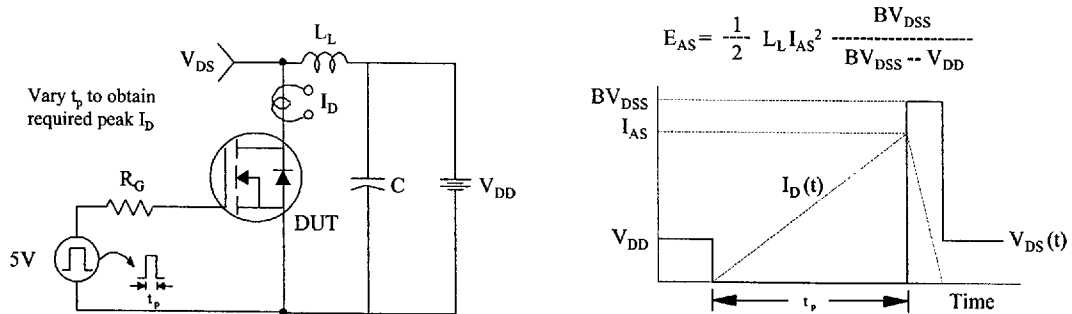


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

